



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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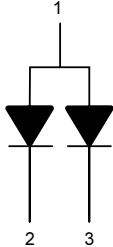
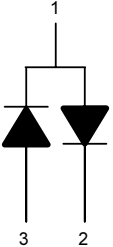
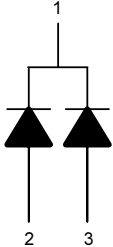
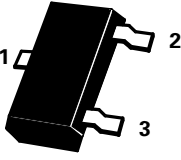
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SOT23 SILICON EPITAXIAL SCHOTTKY BARRIER DIODES

BAT54 SERIES

ISSUE 1- SEPTEMBER 1995

				
BAT54	BAT54A	BAT54S	BAT54C	Device Type
SINGLE	COMMON ANODE	SERIES	COMMON CATHODE	Pin Configuration
L4Z	L42	L44	L43	Partmarking Detail

FEATURES: Low V_F & High Current Capability

APPLICATIONS: PSU, Mobile Telecomms & SCSI

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Continuous Reverse Voltage	V_R	30	V
Forward Current	I_F	200	mA
Forward Voltage @ $I_F = 10\text{mA}$	V_F	400	mV
Repetitive Peak Forward Current	I_{FRM}	300	mA
Non Repetitive Forward Current $t < 1\text{s}$	I_{FSM}	600	mA
Power Dissipation at $T_{amb} = 25^\circ\text{C}$	P_{tot}	330	mW
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$
Junction Temperature \square	T_j	125	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Reverse Breakdown Voltage	$V_{(BR)R}$	30	50		V	$I_R = 10\mu\text{A}$
Forward Voltage	V_F		135 200 280 350 530	240 320 400 500 1000	mV mV mV mV mV	$I_F = 0.1\text{mA}$ $I_F = 1\text{mA}$ $I_F = 10\text{mA}$ $I_F = 30\text{mA}$ $I_F = 100\text{mA}$
Reverse Current	I_R		2.5	4	μA	$V_R = 25\text{V}$
Diode Capacitance	C_D		7.5	10	pF	$f = 1\text{MHz}, V_R = 1\text{V}$
Reverse Recover Time	t_{rr}			5	ns	switched from $I_F = 10\text{mA}$ to $I_R = 10\text{mA}$ $R_L = 100\Omega$, Measured at $I_R = 1\text{mA}$

\square Dual Device; For simultaneous continuous use $T_j = 100^\circ\text{C}$.

TYPICAL CHARACTERISTICS

